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APPLICATION NO.	TION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.			
10/616,863	10/616,863 07/10/2003		Francesco Cerrina	7151	1476			
22922	7590	06/30/2005	EXAMINER					
	T BOERNEI IDA GABRIEI	MOHAMEDULLA, SALEHA R						
	TH WATER ST			ART UNIT	PAPER NUMBER			
SUITE 210	0		1756					
MILWAUK	KEE, WI 5320	02	DATE MAILED: 06/30/2005					

Please find below and/or attached an Office communication concerning this application or proceeding.

		act							
		Application	No.	Applicant(s)					
Office Action Sum	10/616,863		CERRINA ET AL.						
Office Action Sumi	nary	Examiner		Art Unit					
		Saleha R. M		1756					
The MAILING DATE of this Period for Reply	communication appe	ears on the c	over sheet with the c	orrespondence ad	ldress				
A SHORTENED STATUTORY PI THE MAILING DATE OF THIS Co - Extensions of time may be available under the after SIX (6) MONTHS from the mailing date - If the period for reply specified above, the - Failure to reply within the set or extended per Any reply received by the Office later than the earned patent term adjustment. See 37 CFR	OMMUNICATION. e provisions of 37 CFR 1.136 of this communication. than thirty (30) days, a reply will maximum statutory period will riod for reply will, by statute, of ree months after the mailing.	6(a). In no event, within the statutor Il apply and will e cause the applica	however, may a reply be tim y minimum of thirty (30) day: pire SIX (6) MONTHS from iion to become ABANDONEI	nely filed s will be considered timel the mailing date of this co D (35 U.S.C. § 133).					
Status									
 1)⊠ Responsive to communicat 2a)□ This action is FINAL. 3)□ Since this application is in closed in accordance with t 	2b)⊠ This a condition for allowand	action is non	r formal matters, pro		e merits is				
Disposition of Claims									
4a) Of the above claim(s)	·								
Application Papers									
9)☐ The specification is objected	to by the Examiner.								
	10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.								
Applicant may not request that	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).								
	Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).								
11) The oath or declaration is ob	jected to by the Exa	miner. Note	the attached Office	Action or form PT	O-152.				
Priority under 35 U.S.C. § 119									
12) Acknowledgment is made of a) All b) Some * c) No 1. Certified copies of the 2. Certified copies of the 3. Copies of the certified application from the le	one of: e priority documents e priority documents I copies of the priorit	have been r have been r y document	eceived. eceived in Applications have been receive	on No	Stage				
* See the attached detailed Off		•	• • • •	ď.					
Attachment(s)									
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing	Review (PTO-948)	4)	Interview Summary (Paper No(s)/Mail Da						
3) Information Disclosure Statement(s) (PT Paper No(s)/Mail Date 12/11/03.			Notice of Informal Pa		-152)				

DETAILED ACTION

Claims 1-23 are pending.

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1, 2, 6-10, and 16-19 are rejected under 35 U.S.C. 102(b) as being anticipated by US# 5,935,737 to Yan.

Yan teaches EUV mask repair using a photoresist. During the fabrication of a photolithography mask, double defect-absorbing layers are incorporated to ensure the final mask structure is free of defects. The process begins with a resonant reflector substrate. First and second defect-absorbing layers cover the substrate. The first and second defect-absorbing layers are selected to be repairable if defects form, as well as can be etched selectively relative to each other as well as to the underlying substrate. The first defect-absorbing layer is coated with photoresist. The photoresist is patterned using photolithography. Next, the photoresist pattern is transferred to the first defect-absorbing layer through plasma etching. Any defects arising from the etching step are repaired. Next, the pattern formed in the first defect-absorbing layer is transferred to the second defect-absorbing layer, using the first defect-absorbing layer as a mask. Any defects arising from the etching step are repaired. Next, an absorber layer is deposited into the etched open areas of the first and second defect-absorbing layers. The

absorber layer is selected to be substantially absorptive to the wavelength of light to be used on the photolithography mask. The absorber layer is planarized, and then remaining defect-absorbing layers are removed. The remaining mask structure consists of the substrate with a patterned absorber layer.

Allowable Subject Matter

- 3. Claims 11-15 and 22-23 allowed.
- 4. Claims 3-5 and 20-21 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- 5. The prior art does not teach or suggest the method limitations along with the fluorescent material.

Conclusion

6. Any inquiry concerning this communication or earlier communications from the Examiner should be directed to Saleha Mohamedulla whose telephone number is (571) 272-1387. The Examiner can normally be reached Monday-Friday, from 8:00 AM to 4:30 PM. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent

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Saleha R. Molfamedulla

Patent Examiner

Technology Center 1700

June 21, 2005